UNISONIC TECHNOLOGIES CO., LTD

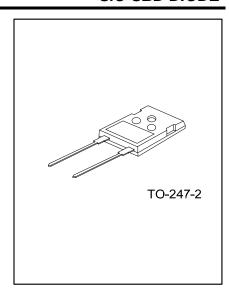
UCBD60120SA

SiC-SBD DIODE

SILICON CARBIDE SCHOTTKY BARRIER DIODES

■ DESCRIPTION

The **UCBD60120SA** is an SiC Schottky barrier diodes (SBDs) feature high reverse voltage ratings. In addition to SBDs with short reverse recovery time (trr), provides 1200V SBDs with a junction barrier Schottky (JBS) structure that provide low leakage current (Ir) and high surge current capability required for switched-mode power supplies. These devices help improve the efficiency of switched-mode power supplies.



■ FEATURES

- * Zero Reverse Recovery Current
- * Humidity Resistant
- * High Frequency Operation
- * Temperature-Independent Switching Behavior

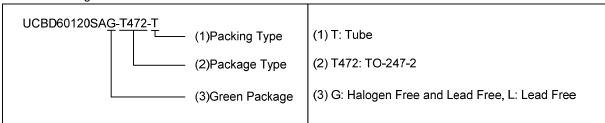
■ SYMBOL



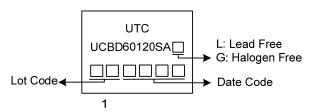
ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment		Da alsima	
Lead Free	Halogen Free	Package	1	2	Packing	
UCBD60120SAL-T472-T	UCBD60120SAG-T472-T	TO-247-2	K	Α	Tube	

Note: Pin Assignment: K: Cathode A: Anode



MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz.

PARAMETER		SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Surge Peak Reverse Voltage		V_{RSM}	1200	V
DC Blocking Voltage		V_R	1200	V
	T _C =25°C	<u> </u>	124	Α
Continuous Forward Current	T _C =135°C	l _F	64	Α
	T _C =140°C	С	60	Α
Repetitive Peak Forward Surge Current	T _J =25°C t _P =10ms, Half Sine Wave	I _{FRM}	488	А
Non-Repetitive Peak Forward Surge	T _J =25°C t _P =10ms, Half Sine Wave		538	А
Current	T _J =110°C t _P =10ms, Half Sine Wave	Ігѕм	511	А
	T _C =25°C	P _D	517	W
Power Dissipation	T _C =110°C		224	W
•	T _C =150°C		86	W
Operating Junction Temperature		TJ	-55 ~ +175	°C
Storage Temperature Range		T _{STG}	-55 ~ +175	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

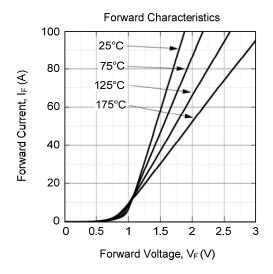
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θις	0.29	°C/W

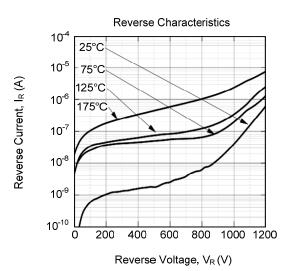
■ ELECTRICAL CHARACTERISTICS

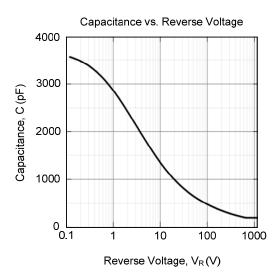
(Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz)

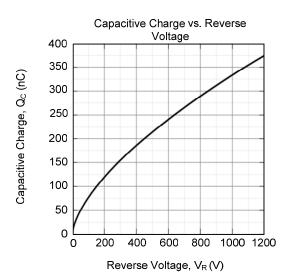
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC Blocking Voltage	V_{DC}	T _C =25°C	1200			V
	V _F	I _F =30A, T _J =25°C		1.25		V
Forward Voltage		I _F =60A, T _J =25°C		1.51	1.7	V
		I _F =60A, T _J =175°C		2.18		V
Reverse Current	I _R	V _R =1200V, T _J =25°C		5	100	μΑ
Reverse Current		V _R =1200V, T _J =175°C		10		μΑ
Total Capacitive Charge	Qc	V _R =800V		290		nC
	С	V _R =1V, f=1MHz		2884		pF
Total Capacitance		V _R =400V, f=1MHz		251		pF
		V _R =800V, f=1MHz		198		pF
Capacitance Stored Energy	Ec	V _R =800V		64		μJ

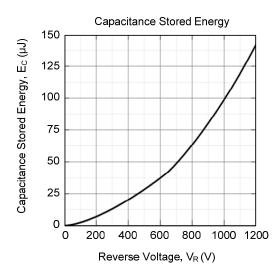
■ TYPICAL CHARACTERISTICS

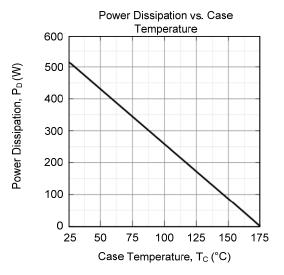




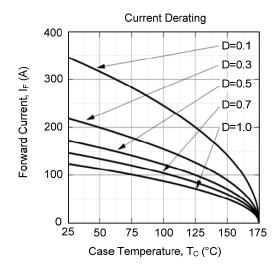








■ TYPICAL CHARACTERISTICS (Cont.)



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